27. (new) The method of claim 26 wherein the silicon containing dielectric layer includes fluorosilicate glass (FSG).

28. (new) The method of claim 27 wherein the plasma enhanced chemical vapor deposition (PECVD) includes high density plasma chemical vapor deposition (HDP-CVD) methods.

29. (new) The method of claim 27 wherein the silicon containing dielectric layer is formed to a thickness of from about 4,000 to about 24,000 angstroms.

30. (new) The method of claim 27 wherein the temperature is controlled within a range of from about 350 to about 450 degrees centigrade.

31. (new) The method of claim 27, wherein the backside cooling gas is comprised of helium.

32. (new) The method of claim 27, wherein the backside cooling gas pressure is from about 2 to 10 torr.

33. (new) The method of claim 27, wherein the backside cooling gas pressure is from about 2 to 10 torr, the temperature of the substrate is from about 380 to 450 degrees centigrade, and the silicon containing dielectric layer is comprised of FSG.

34. (new) The method of claim 27, wherein formation of the PECVD silicon containing layer is achieved at a bias sputtering power of from about 100 to 4,000 watts.